# **ON Semiconductor®**



Title of Change:	Gresham Devices as Drop-In Replacements for Current FAB2 Devices - NCV8772 family					
Proposed Changed Material First Ship Date:	12 Mar 2022 or earlier if approved by customer					
Current Material Last Order Date:	30 Jun 2021 Orders received after the Current Material Last Order Date expiration are to be considered as orders for new changed material as described in this PCN. Orders for current (unchanged) material after this date will be per mutual agreement and current material inventory availability.					
Current Material Last Delivery Date:	11 Mar 2022, unless otherwise mutually agreed. The Current Material Last Delivery Date may be subject to change based on build and depletion of the current (unchanged) material inventory					
Product Category:	Active components – Integrated circuits					
Contact information:	Contact your local ON Semiconductor Sales Office or Juraj.Kremmer@onsemi.com					
PCN Samples Contact:	Contact your local ON Semiconductor Sales Office to place sample order or < <u>PCN.samples@onsemi.com</u> >. Sample requests are to be submitted no later than 45 days after publication of this change notification. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.					
Sample Availability Date:	26 Mar 2021					
PPAP Availability Date:	26 Apr 2021					
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or Tomas.Vajter@onsemi.com					
Type of Notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 12 months prior to implementation of the change or earlier upon customer approval. ON Semiconductor will consider this proposed change and it's conditions acceptable, unless an inquiry is made in writing within 45 days of delivery of this notice. To do so, contact PCN.Support@onsemi.com.					
Change Category						
Category	Type of Change					
Design	Change in process technology (e. g. process changes like lithography, etch. oxide deposition.					
Process - Wafer Production	diffusion, die back surface preparation/backgrind,), Move of all or part of wafer fab to a different location/site/subcontractor, New wafer diameter					
Data Sheet	Change of datasheet parameters/electrical specification (min./max./typ. values) and/or AC/DC specification					
Process - Assembly	Change of mold compound, Change of wire bonding, Change of product marking					

## Description and Purpose:

Change of design to new wafer technology to support new wafer technology. Change of wafer processing technology from PS5B currently manufactured in Fab2, Oudenaarde, Belgium (150 mm fab) to I3T50 in Gresham, Oregon, USA (200 mm fab). Old PS5B technology replaced by the more advanced I3T50 wafer process. PS5B wafer technology is nearing end of life and cannot support future production needs. These changes are also related to the Fab2 manufacturing site sale.

In addition, package changes were done to improve delamination performance.

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			Before Cha	nge Description	After Change Des	cription			
			DPAK: NCV87722D	DT33RKG,	DPAK: NCV8772CDT334RKG,				
OPN			NCV87722DT50RKG		NCV8772CDT504RKG				
			D2PAK: NCV87722D	5S33R4G	D2PAK: NCV8772CDS334R4G				
	Wafer Fab location		Fab2, Oude	naarde, Belgium	Gresham, Orego	n, USA			
	Wafer Technology		PS5E	3 (1.5um)	I3T50 (0.35u	m)			
	Wafer Diameter		1	50mm	200mm				
	Bond Wire (DPAK)		Cu	2.0 mil	Cu 1.5 mil				
Mo	old Compound (DPAK)		GE 80	000CH4ES	G700HF				
Mo	ld Compound (D2PAK)			G600	G700HF				
				<b>F</b> ue	Ta				
				Lipo1: 7722226		1.7720240			
Dro	oduct marking change			- Line1: 7722336	NCV8772CDT504RKG - Line	1: 772C34G			
	ouuct marking change		NCV87722D150000	- Line 2. V8772230	NCV8772CDS334R4G - Line	2. 772C340 2. V8772C34			
Reason / Mo	tivation for Change:	Benefit wafer fa Risk for Quality	of the change: More r b capacity. Improved Late Release: Possible Improvement: Yes Lo	nodern wafer technology t package BOM. Improved p e supply disruptions.	hat will supported long term v arametric performance. ved package delamination peri	vith improved			
		Quanty	improvement. res. ee			iormanee.			
Anticipated impact on fit, form, function, reliability, productThe de succesfunction, reliability, product safety or manufacturability:The de			vice has been qualified and validated based on the same Product Specification. The device has fully passed the qualification tests. Potential impacts can be identified, but due to testing ned by ON Semiconductor in relation to the PCN, associated risks are verified and excluded.						
		NO antic	ipateu impacts.						
Sites Affected	d:								
ON Semiconductor Sites External Foundry/Subcon Sites									
ON Semicondu	ctor Gresham, Oregon, U	SA		None					
ON Semicondu	ctor Oudenaarde, Belgiur	n							
ON Semicondu	ctor Seremban, Malaysia								
Marking of Parts/ Traceability of New part nu NCV8772CD NCV8772CD NCV8772CD NCV8772CD NCV8772CD			rt numbers will have a 2CDT334RKG - Line1: 2CDT504RKG - Line1: 2CDS334R4G – Line2:	new package topside marl 772C34G 772C54G V8772C34	king:				
Reliability Da	ta Summary:								
QV DEVICE NAME: <u>NCV8772CDT504RKG / NCV8775CDT50RKG</u> RMS: <u>S57655 / S49712, S58942</u>									
PACKAGE: DPA	PACKAGE: <u>DPAK 5LD</u>								
lest	Specification	1	- 10-22-11	Condition	Interval	Results			
HTOL	JESD22-A108		Ta = 125°C, Vcc = 4	40V	2016 hrs	0/240			
HTSL	JESD22-A103		la = 150°C		2016 hrs	0/252			
	JESD22-A104		Ta = -65°C to+150	<u>ັ</u> ເ	1000 cyc	0/252			
	JESD22 A105		$Ia = -40^{\circ}C to + 125$	L 10 9 main 1/22 401/	1000 cyc	0/45			
HASI	JESD22-A110		$Ta = 130^{\circ}C, 85\% R$	$\Pi$ , 18.8pSig, VCC = 4UV	96 nrs	0/252			
	JESUZZ-A110		$Ta = 110^{\circ}C, 85\% R$	H 19 Posig upbiasod	264 Nrs	0/252			
	JESUZZ-AII8 חדא ו גרב_۸113 ו	-020	1a - 150 C, δ5% K	ii, to.ohsik, niinigsen	192 1112	0/252			
SD		520	Ta = 2450.5 sec			0/45			
	JSTD002 Ta = 245C, 5 S					<i>u</i> , <i>u</i>			



## QV DEVICE NAME: <u>NCV8772CDS334R4G / NCV8775CDS50R4G</u> RMS: <u>S57654 / S58945, S63707, S65110, S66494</u>

PACKAGE: D2P	PAK 5LD			
Test	Specification	Condition	Interval	Results
HTOL	JESD22-A108	Ta = 125°C, Vcc = 40V	2016 hrs	0/240
HTSL	JESD22-A103	Ta = 150°C	2016 hrs	0/252
TC	JESD22-A104	Ta = -65°C to+150°C	1000 cyc	0/252
PTC	JESD22 A105	Ta = -40°C to+125°C	1000 cyc	0/55
HAST	JESD22-A110	Ta = 110°C, 85% RH, 18.8psig, Vcc = 40V	264 hrs	0/252
uHAST	JESD22-A118	Ta = 130°C, 85% RH, 18.8psig, unbiased	192 hrs	0/252
PC	JESD-A113, J-STD-020	MSL= 1 @ 260°C		
SD	JSTD002	Ta = 245C, 5 sec		0/45

## NOTE: AEC-1pager is attached.

To view attachments:

1. Download pdf copy of the PCN to your computer

2. Open the downloaded pdf copy of the PCN

3. Click on the paper clip icon available on the menu provided in the left/bottom portion of the screen to reveal the Attachment field

4. Then click on the attached file.

## **Electrical Characteristics Summary:**

## **Datasheet Maximum Ratings updated as follows**

		NCV8	3772C			NCV8772					
Rating	Symbol	Min	Max	Unit	Symbol	Min	Max	Unit			
ABSOLUTE MAXIMUM RATINGS			_								
Input Voltage DC	Vin	-0.3	40	v	Vin	-0.3	40	v			
Input Voltage Load Dump - Suppressed	V,	-	45		V,	-	45				
Input Current					lin	-5	-	mA			
Output Voltage	Vout	-0.3	7	v	Vout	-0.3	5.5	V			
Output Current					lout	-3	Current Limited	mA			
Enable Input Voltage DC	V <sub>EN</sub>	-0.3	40	V	V <sub>EN</sub>	-0.3	40	V			
Transient, t < 100 ms							45				
Enable Input Current					I <sub>EN</sub>	-1	1	mA			
DT (Reset Delay Time Select) Voltage					V <sub>DT</sub>	-0.3	5.5	V			
DT (Reset Delay Time Select) Current					I <sub>DT</sub>	-1	1	mA			
Reset Output Voltage	VRD	-0.3	7	V	V <sub>RD</sub>	-0.3	5.5	V			
Reset Output Current					IRD	-3	3	mA			
Junction Temperature Range	Tj	-40	150	°C	T	-40	150	°C			
Storage Temperature Range	T <sub>STG</sub>	-55	150	°C	T <sub>STG</sub>	-55	150	°C			

#### ESD CAPABILITY

ESD Capability, Human Body Model	ESD <sub>HBM</sub>	-4	4	kV	ESD <sub>HBM</sub>	-2	2	kV			
ESD Capability, Charged Device Model	ESD <sub>CDM</sub>	-1	1	kV	ESD <sub>CDM</sub>	-1	1	kV			
ESD Capability, Machine Model					ESD <sub>MM</sub>	-200	200	V			



LECTRICAL CHARACTERISTICS NCV8772C						NCV8772							
Parameter		Test Conditions	Symbol	Min	Тур	Max	Unit	Test Conditions	Symbol	Min	Тур	Max	Unit
EGULATOR OUTPUT		1											
utput Voltage (Accuracy %)			Vout	(-2%)		(+2 %)	v		Vout	(-2 %)		(+2%)	V
	3.3 V	$V_{in}$ = 4.5 V to 40 V, $I_{out}$ = 0.1 mA to 200 mA		3.234	3.3	3.366		$V_{\rm in}$ = 4.5 V to 40 V, $I_{\rm out}$ = 0.1 mA to 200 mA		3.234	3.3	3.366	
		$V_{\rm in}$ = 4.5 V to 16 V, $I_{\rm out}$ = 0.1 mA to 350 mA		3.234	3.3	3.366		$V_{\rm in}$ = 4.5 V to 16 V, $I_{\rm out}$ = 0.1 mA to 350 mA		3.234	3.3	3.366	
	5.0V	$V_{in} = 5.6 V$ to 40 V, $I_{out} = 0.1 \text{ mA}$ to 200 mA		4.9	5.0	5.1		$V_{in} = 5.6 V$ to 40 V, $I_{out} = 0.1 \text{ mA}$ to 200 mA		4.9	5.0	5.1	
		V <sub>in</sub> = 5.975 V to 16 V, I <sub>out</sub> = 0.1 mA to 350 mA		4.9	5	5.1		$V_{in} = 5.975 V \text{ to } 16 V$ , $I_{out} = 0.1 \text{ mA to } 350 \text{ mA}$		4.9	5.0	5.1	
utput Voltage (Accuracy %)								T <sub>1</sub> = 25°C to 125℃	Vout	(-1.5%)		(+1.5 %)	v
	3.3V							V <sub>in</sub> = 4.5V to 16V, I <sub>nut</sub> = 0.1 mA to 200 mA		3.2505	3.3	3.3495	
	5.0V							V <sub>in</sub> = 5.575 V to 16 V, I <sub>nut</sub> = 0.1 mA to 200 mA		4.925	5	5.075	
tput Voltage (Accuracy %)								T <sub>J</sub> = -40°C to 125°C	Vout	(-2%)		(+2%)	v
	3.3V							Via = 4.5 V to 28 V. Luc = 0mA to 350 mA		3.234	3.3	3.366	
	5.0V							V = 5.975 V to 28 V. L = 0 mA to 350 mA		4.9	5	5.1	
onout Voltage			V~				mV	1 m	Vee		-		mV
-post ronge	5 O V	L = 200 mA			250	450		L . = 200 mA	.00		250	500	
	2.01	L = 350 mA			440	800		L = 350 mA			440	875	
utout Canacitor for Stability		fait - 220 mit						L = 0 mA to 350 mA				5.5	
apper opportion to to appendix,								Taat - Office as SSO for t	~			100	
									ESR	0.01		100	
DISABLE AND QUIESCENT CU	RRENTS								2011	0.01			
Disable Current		V <sub>EN</sub> = 0 V, TJ < 125°C	IDIS	-	-	1	μA	V <sub>EN</sub> = 0 V, TJ < 85°C	lois	-	-	1	۵μ
Quiescent Current (I <sub>a</sub> = I <sub>in</sub> - I <sub>out</sub> )			I <sub>q</sub>				μA		l <sub>g</sub>				μA
		I <sub>out</sub> = 0 mA, T <sub>J</sub> = 25°C		-	18	22		I <sub>out</sub> = 0.1 mA, T <sub>J</sub> = 25°C		-	24	29	
		l <sub>out</sub> = 0 mA, T <sub>i</sub> ≤ 125°C		-	-	24		I <sub>aut</sub> = 0.1 mA to 350 mA, T <sub>1</sub> ≤ 125°C		-	-	30	
		I <sub>out</sub> = 0.1 mA, T <sub>J</sub> = 25 °C			20	24							
		I <sub>out</sub> = 0.1 mA, T <sub>1</sub> ≤ 125°C		-		26							
PSRR													
Power Supply Ripple Rejection		f = 100 Hz, 0.5 V <sub>pp</sub>	PSRR	-	75	-	dB	f = 100 Hz, 0.5 V <sub>pp</sub>	PSRR	-	60	-	dB
ENABLE THRESHOLDS													
Enable Input Threshold Voltage			V <sub>th(EN)</sub>				v		V <sub>th(EN)</sub>				v
Logic Low				0.8	1.65	-				-	-	0.8	
Logic High				-	1.75	2.5	<u> </u>	┥┝━━━━━	_	2.5	-	-	
Enable Input Current							μΑ		Ι.				μ
Logic High		V <sub>EN</sub> = 5 V	I <sub>EN_ON</sub>	-	3	5		V <sub>EN</sub> = 5 V	I <sub>EN_ON</sub>	-	3	5	
Logic Low		V <sub>EN</sub> = 0 V	LEN_OFF	-	0.5	1		V <sub>EN</sub> = 0V, TJ < 85°C	EN_OFF	-	0.5	1	

## **List of Affected Parts:**

**Note:** Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

Current Part Number	New Part Number	Qualification Vehicle
NCV87722DT33RKG	NCV8772CDT334RKG	NCV8772CDT504RKG
NCV87722DT50RKG	NCV8772CDT504RKG	NCV8772CDT504RKG
NCV87722D5S33R4G	NCV8772CDS334R4G	NCV8772CDS334R4G